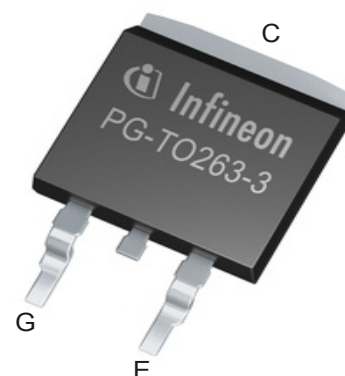


High speed switching series fifth generation

## High speed FAST IGBT in TRENCHSTOP™ 5 technology

### Features and Benefits:

- High speed F5 technology offering:
- Best-in-Class efficiency in hard switching and resonant topologies
  - 650V breakdown voltage
  - Low gate charge  $Q_G$
  - Maximum junction temperature 175°C
  - Dynamically stress tested
  - Qualified according to AEC-Q101
  - Green package (RoHS compliant)
  - Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>



### Applications:

- Off-board charger
- On-board charger
- DC/DC converter
- Power-factor correction

### Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



### Key Performance and Package Parameters

Type	$V_{CE}$	$I_C$	$V_{CEsat}, T_{vj}=25^{\circ}C$	$T_{vjmax}$	Marking	Package
AIGB50N65F5	650V	50A	1.6V	175°C	AG50EF5	PG-TO263-3



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## High speed switching series fifth generation

## Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	$V_{CE}$	650	V
DC collector current, limited by $T_{vjmax}$ $T_c = 25^{\circ}\text{C}$ value limited by bondwire $T_c = 100^{\circ}\text{C}$	$I_C$	80.0 56.0	A
Pulsed collector current, $t_p$ limited by $T_{vjmax}^{1)}$	$I_{Cpuls}$	150.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$ , $T_{vj} \leq 175^{\circ}\text{C}$ , $t_p = 1\mu\text{s}^{1)}$	-	150.0	A
Gate-emitter voltage Transient Gate-emitter voltage ( $t_p \leq 10\mu\text{s}$ , $D < 0.010$ )	$V_{GE}$	$\pm 20$ $\pm 30$	V
Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$	$P_{tot}$	305.0 152.5	W
Operating junction temperature	$T_{vj}$	-40...+175	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-55...+150	$^{\circ}\text{C}$
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020)		260	$^{\circ}\text{C}$

## Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

 $R_{th}$  Characteristics

IGBT thermal resistance, junction - case	$R_{th(j-c)}$		-	-	0.50	K/W
Thermal resistance, min. footprint junction - ambient	$R_{th(j-a)}$		-	-	65	K/W
Thermal resistance, 6cm <sup>2</sup> Cu on PCB junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

## Static Characteristic

Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}$ , $I_C = 0.20\text{mA}$	650	-	-	V
Collector-emitter saturation voltage	$V_{CEsat}$	$V_{GE} = 15.0\text{V}$ , $I_C = 50.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- - -	1.60 1.80 1.90	2.10 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.50\text{mA}$ , $V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	$I_{CES}$	$V_{CE} = 650\text{V}$ , $V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	- 1000	40 -	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{V}$ , $V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE} = 20\text{V}$ , $I_C = 50.0\text{A}$	-	50.0	-	S

<sup>1)</sup> Defined by design. Not subject to production test.

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Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	3000	-	pF
Output capacitance	$C_{oes}$		-	65	-	
Reverse transfer capacitance	$C_{res}$		-	11	-	
Gate charge	$Q_G$	$V_{CC} = 520\text{V}, I_C = 50.0\text{A}, V_{GE} = 15\text{V}$	-	115.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	7.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic, at <math>T_{vj} = 25^{\circ}\text{C}</math></b>						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C}, V_{CC} = 400\text{V}, I_C = 25.0\text{A}, V_{GE} = 0.0/15.0\text{V}, R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega, L_{\sigma} = 30\text{nH}, C_{\sigma} = 30\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	23	-	ns
Rise time	$t_r$		-	16	-	ns
Turn-off delay time	$t_{d(off)}$		-	166	-	ns
Fall time	$t_f$		-	13	-	ns
Turn-on energy	$E_{on}$		-	0.55	-	mJ
Turn-off energy	$E_{off}$		-	0.11	-	mJ
Total switching energy	$E_{ts}$		-	0.66	-	mJ
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C}, V_{CC} = 400\text{V}, I_C = 6.0\text{A}, V_{GE} = 0.0/15.0\text{V}, R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega, L_{\sigma} = 30\text{nH}, C_{\sigma} = 30\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	20	-	ns
Rise time	$t_r$		-	5	-	ns
Turn-off delay time	$t_{d(off)}$		-	172	-	ns
Fall time	$t_f$		-	28	-	ns
Turn-on energy	$E_{on}$		-	0.13	-	mJ
Turn-off energy	$E_{off}$		-	0.04	-	mJ
Total switching energy	$E_{ts}$		-	0.17	-	mJ

## High speed switching series fifth generation

## Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic, at <math>T_{vj} = 150^{\circ}\text{C}</math></b>						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C}$ , $V_{CC} = 400\text{V}$ , $I_C = 25.0\text{A}$ , $V_{GE} = 0.0/15.0\text{V}$ , $R_{G(on)} = 12.0\Omega$ , $R_{G(off)} = 12.0\Omega$ , $L\sigma = 30\text{nH}$ , $C\sigma = 30\text{pF}$ $L\sigma$ , $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	22	-	ns
Rise time	$t_r$		-	17	-	ns
Turn-off delay time	$t_{d(off)}$		-	179	-	ns
Fall time	$t_f$		-	9	-	ns
Turn-on energy	$E_{on}$		-	0.74	-	mJ
Turn-off energy	$E_{off}$		-	0.15	-	mJ
Total switching energy	$E_{ts}$		-	0.89	-	mJ
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C}$ , $V_{CC} = 400\text{V}$ , $I_C = 6.0\text{A}$ , $V_{GE} = 0.0/15.0\text{V}$ , $R_{G(on)} = 12.0\Omega$ , $R_{G(off)} = 12.0\Omega$ , $L\sigma = 30\text{nH}$ , $C\sigma = 30\text{pF}$ $L\sigma$ , $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	19	-	ns
Rise time	$t_r$		-	6	-	ns
Turn-off delay time	$t_{d(off)}$		-	205	-	ns
Fall time	$t_f$		-	19	-	ns
Turn-on energy	$E_{on}$		-	0.21	-	mJ
Turn-off energy	$E_{off}$		-	0.06	-	mJ
Total switching energy	$E_{ts}$		-	0.27	-	mJ

High speed switching series fifth generation

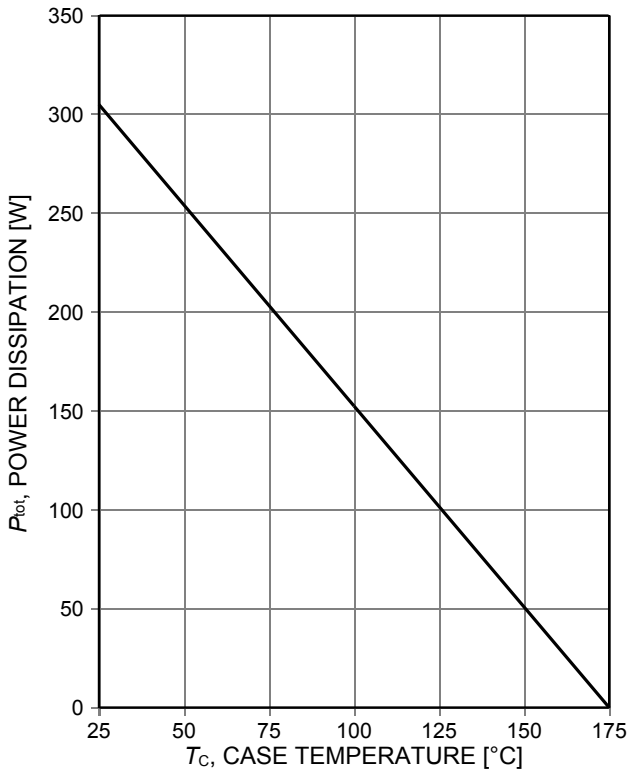


Figure 1. Power dissipation as a function of case temperature ( $T_{vj} \leq 175^\circ\text{C}$ )

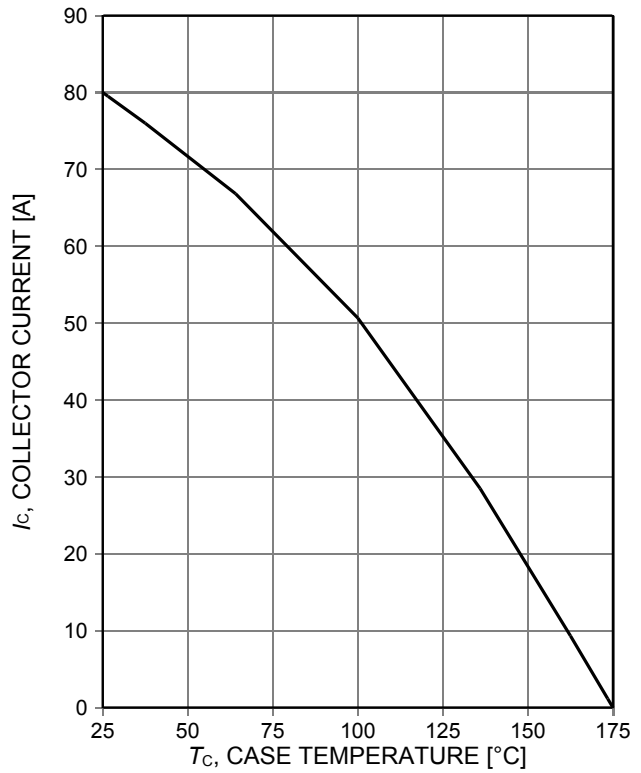


Figure 2. Collector current as a function of case temperature ( $V_{GE} \geq 15\text{V}$ ,  $T_{vj} \leq 175^\circ\text{C}$ )

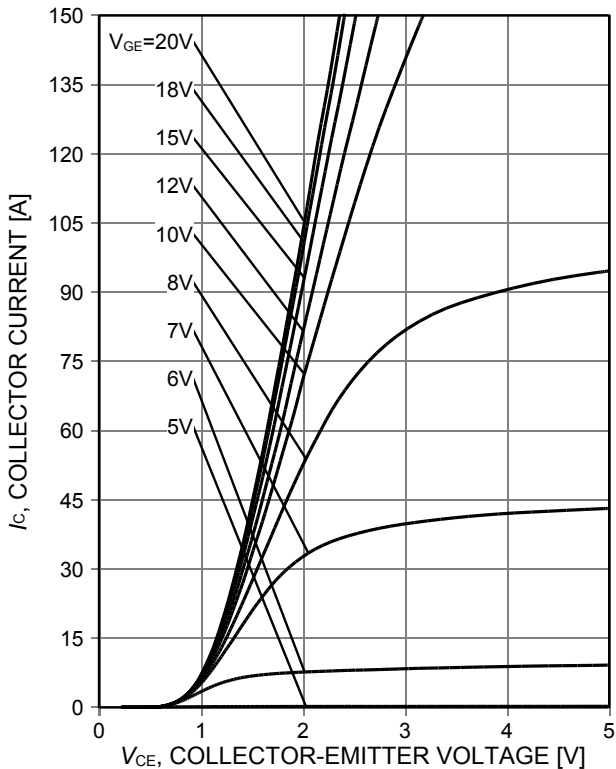


Figure 3. Typical output characteristic ( $T_{vj} = 25^\circ\text{C}$ )

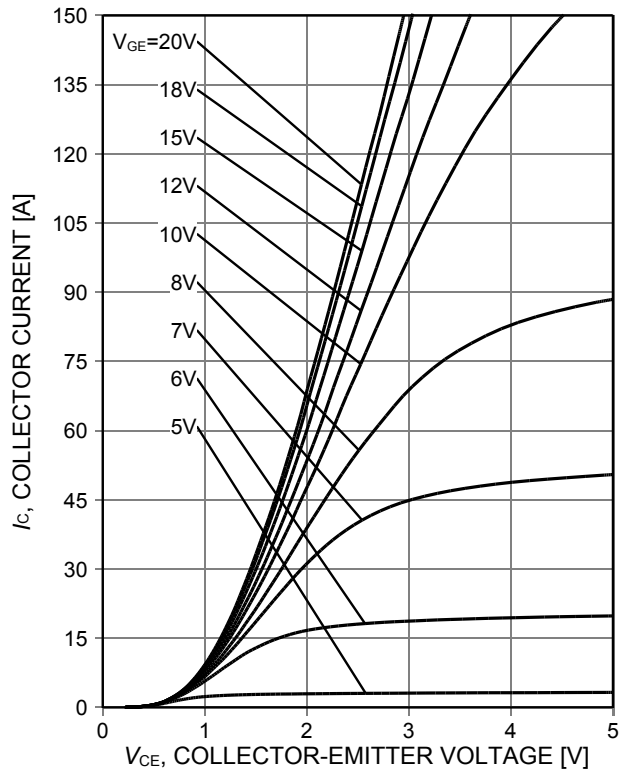


Figure 4. Typical output characteristic ( $T_{vj} = 150^\circ\text{C}$ )

High speed switching series fifth generation

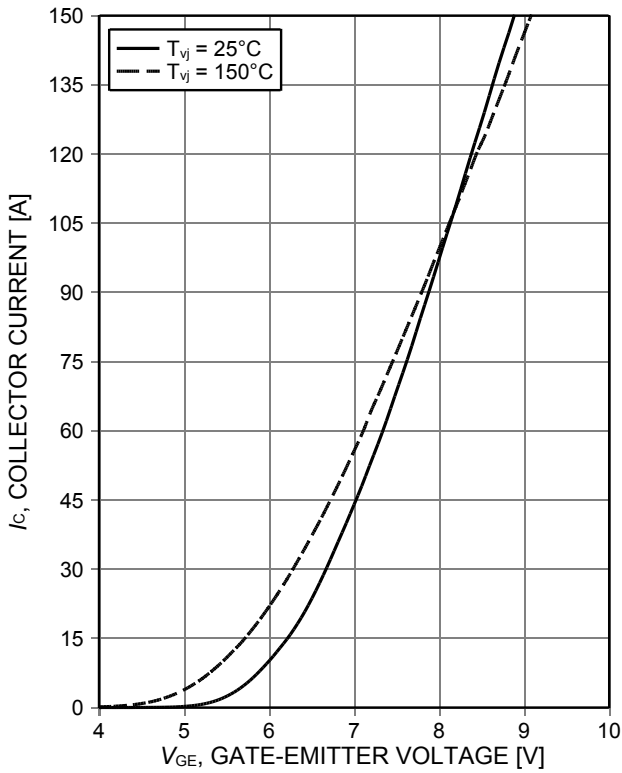


Figure 5. Typical transfer characteristic (V<sub>CE</sub>=20V)

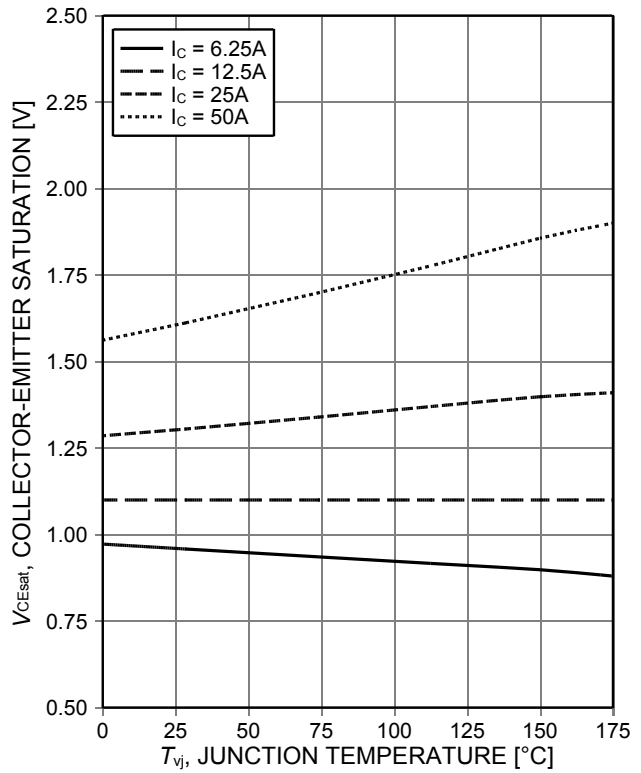


Figure 6. Typical collector-emitter saturation voltage as a function of junction temperature (V<sub>GE</sub>=15V)

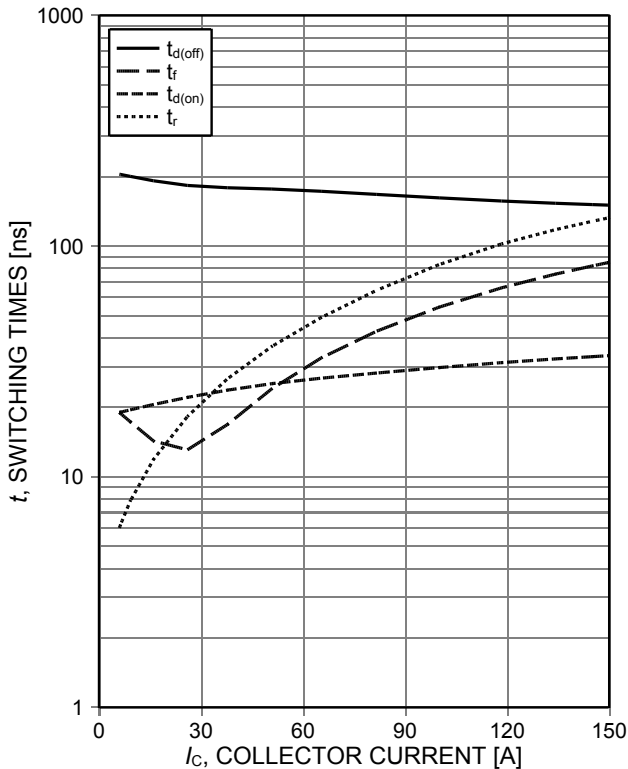


Figure 7. Typical switching times as a function of collector current (inductive load, T<sub>vj</sub>=150°C, V<sub>CE</sub>=400V, V<sub>GE</sub>=15/0V, r<sub>G</sub>=12Ω, Dynamic test circuit in Figure E)

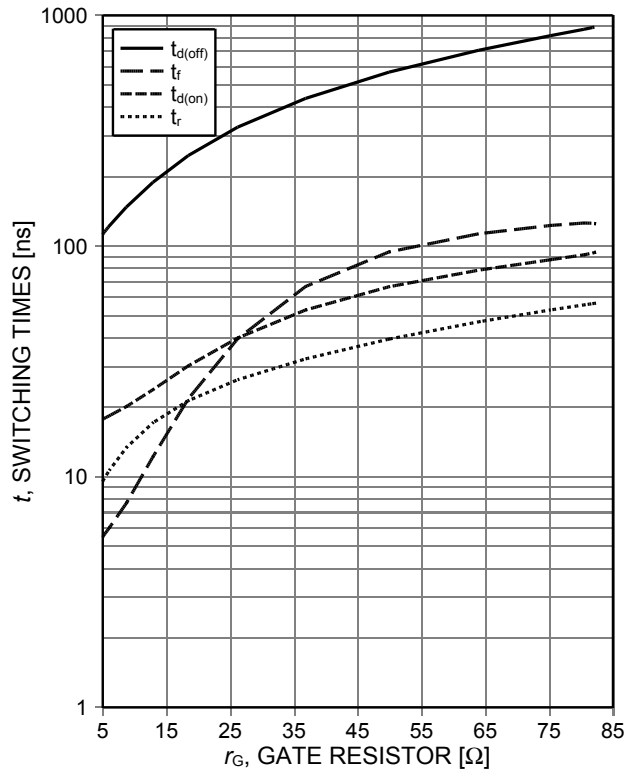


Figure 8. Typical switching times as a function of gate resistor (inductive load, T<sub>vj</sub>=150°C, V<sub>CE</sub>=400V, V<sub>GE</sub>=15/0V, Ic=25A, Dynamic test circuit in Figure E)

High speed switching series fifth generation

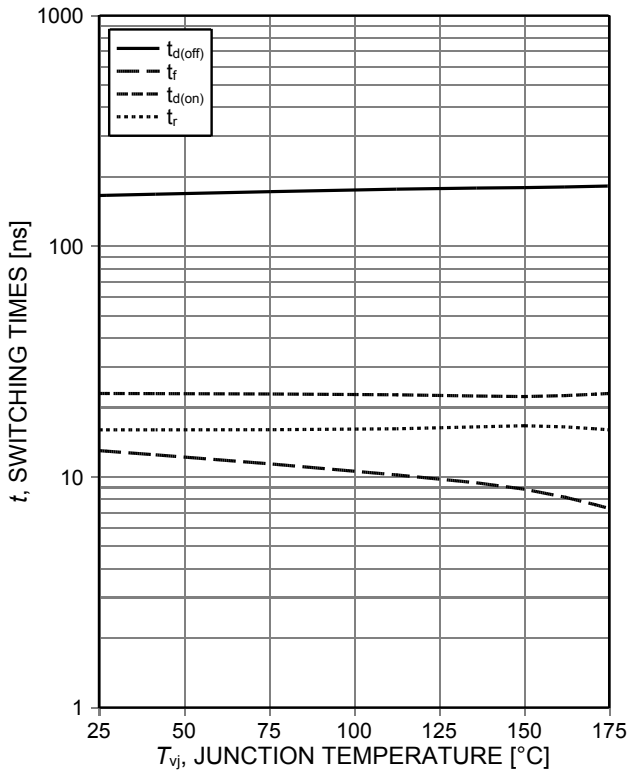


Figure 9. Typical switching times as a function of junction temperature (inductive load,  $V_{CE}=400V$ ,  $V_{GE}=15/0V$ ,  $I_C=25A$ ,  $r_G=12\Omega$ , Dynamic test circuit in Figure E)

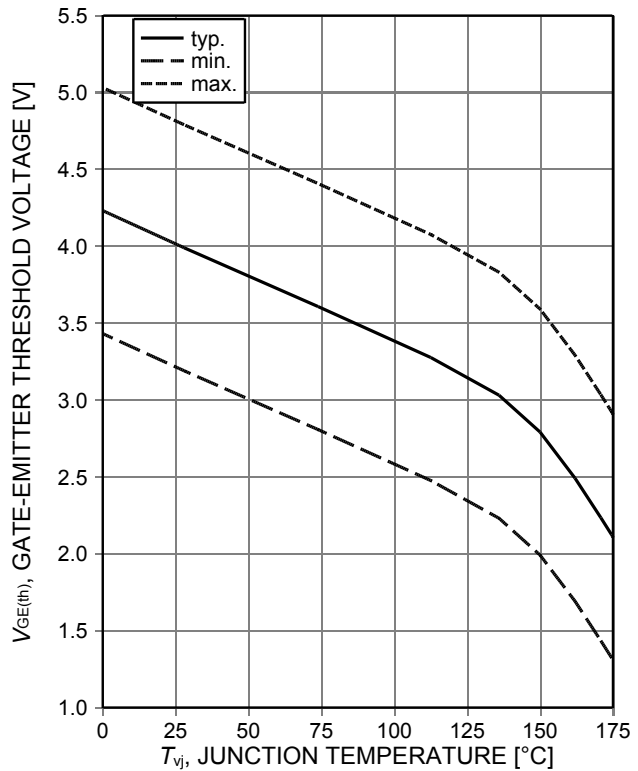


Figure 10. Gate-emitter threshold voltage as a function of junction temperature ( $I_C=0.5mA$ )

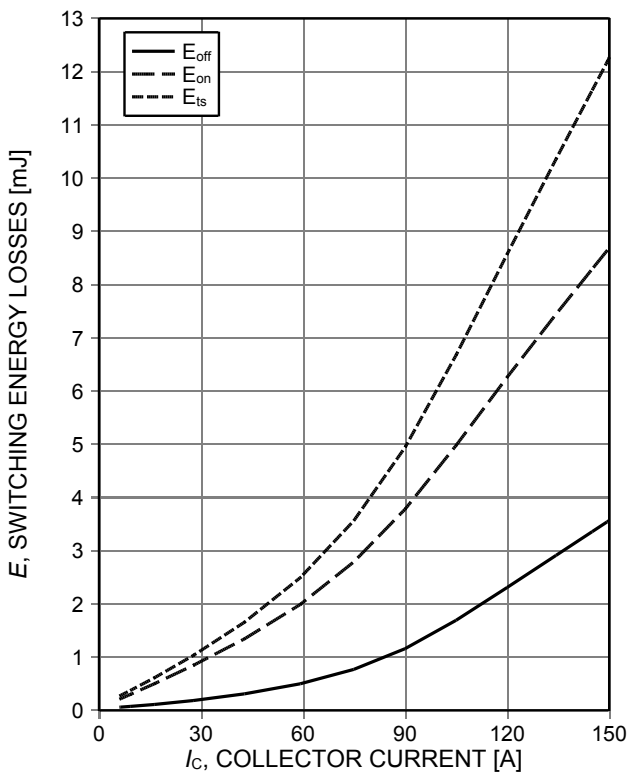


Figure 11. Typical switching energy losses as a function of collector current (inductive load,  $T_{vj}=150^\circ C$ ,  $V_{CE}=400V$ ,  $V_{GE}=15/0V$ ,  $r_G=12\Omega$ , Dynamic test circuit in Figure E)

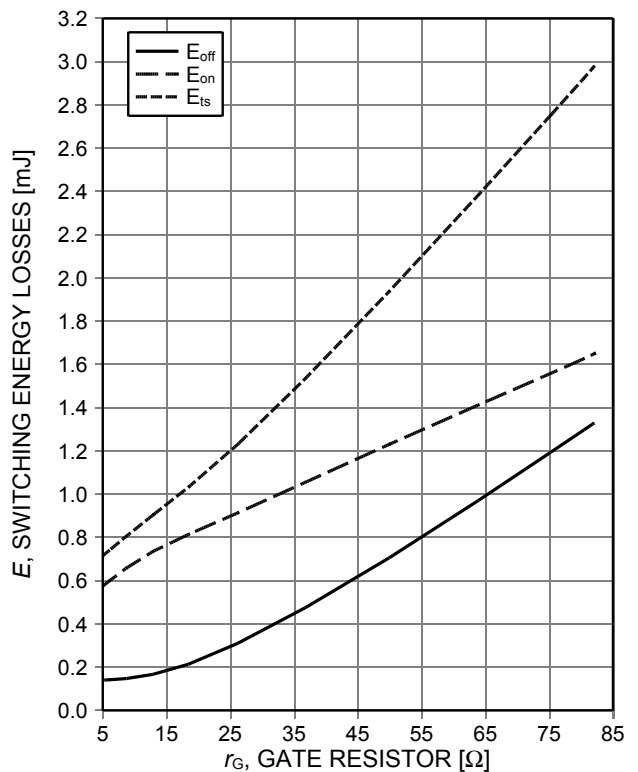


Figure 12. Typical switching energy losses as a function of gate resistor (inductive load,  $T_{vj}=150^\circ C$ ,  $V_{CE}=400V$ ,  $V_{GE}=15/0V$ ,  $I_C=25A$ , Dynamic test circuit in Figure E)



High speed switching series fifth generation

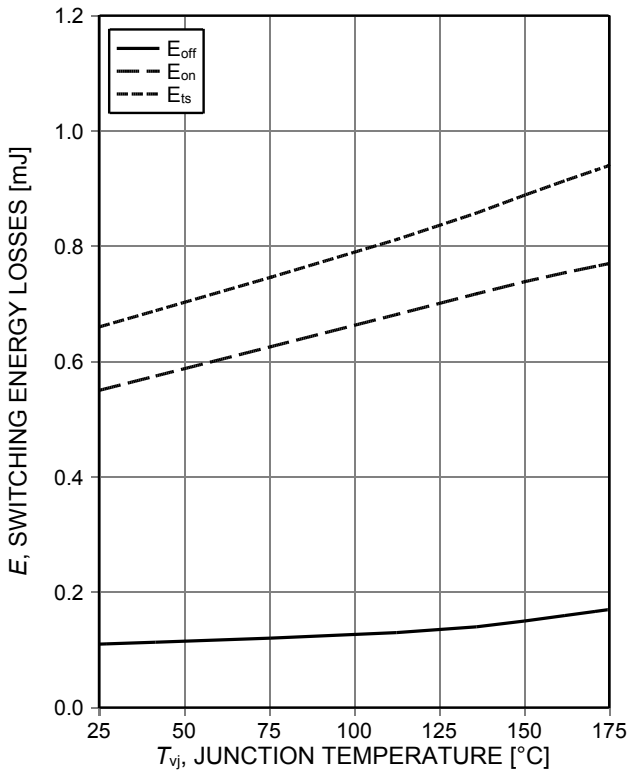


Figure 13. **Typical switching energy losses as a function of junction temperature** (inductive load,  $V_{CE}=400V$ ,  $V_{GE}=15/0V$ ,  $I_C=25A$ ,  $r_G=12\Omega$ , Dynamic test circuit in Figure E)

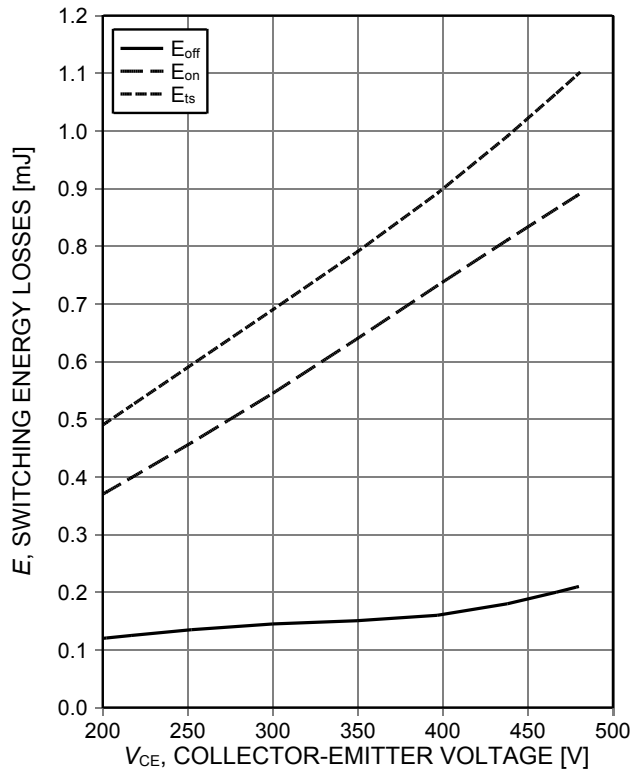


Figure 14. **Typical switching energy losses as a function of collector emitter voltage** (inductive load,  $T_{vj}=150^\circ C$ ,  $V_{GE}=15/0V$ ,  $I_C=25A$ ,  $r_G=12\Omega$ , Dynamic test circuit in Figure E)

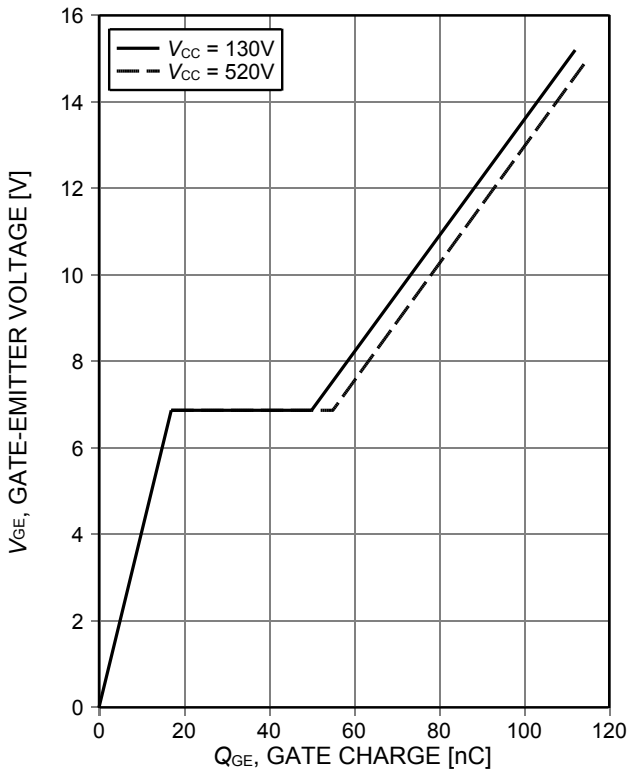


Figure 15. **Typical gate charge** ( $I_C=50A$ )

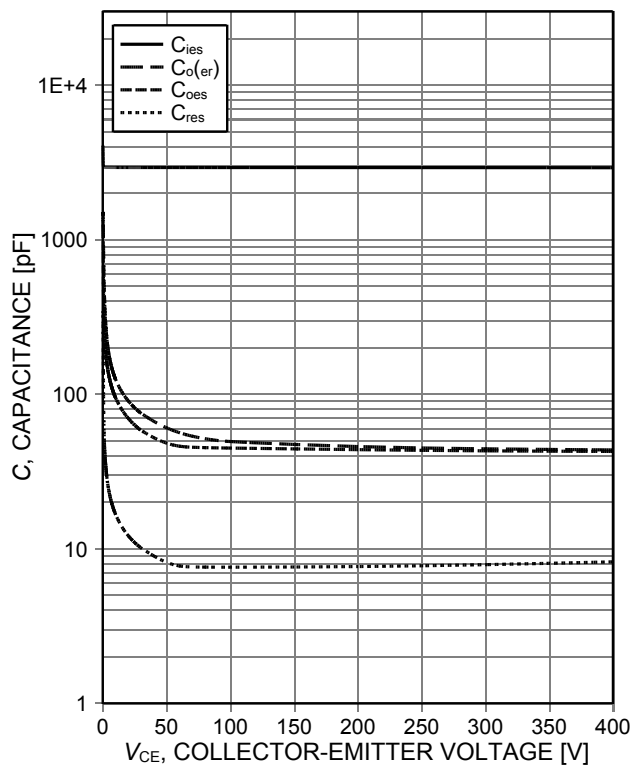


Figure 16. **Typical capacitance as a function of collector-emitter voltage** ( $V_{GE}=0V$ ,  $f=1MHz$ )

High speed switching series fifth generation

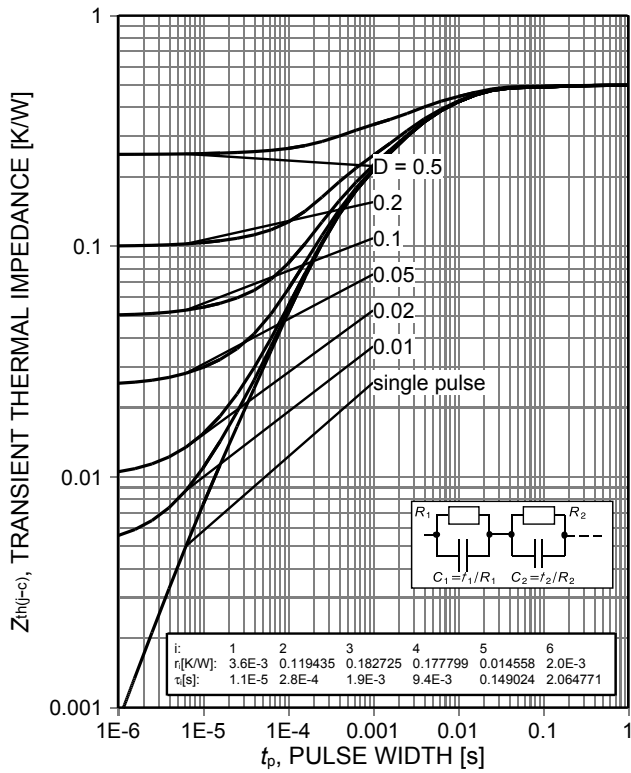
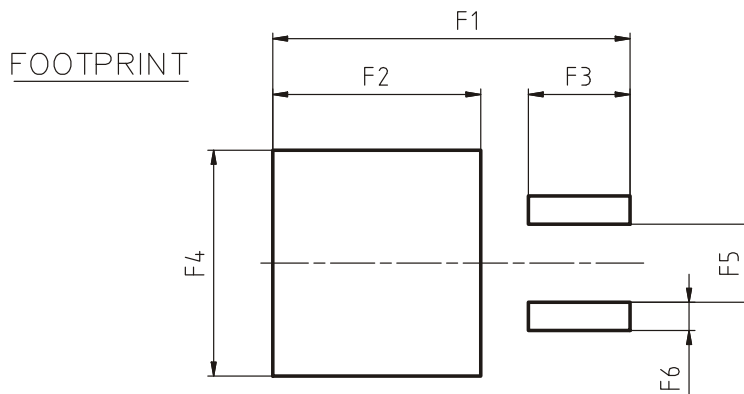
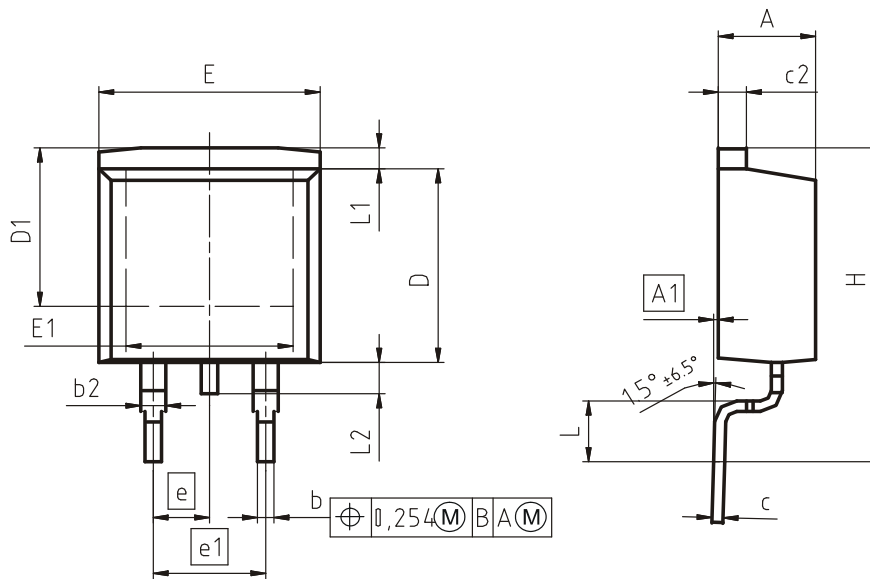


Figure 17. IGBT transient thermal impedance ( $D=t_p/T$ )

Package Drawing PG-TO263-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

DOCUMENT NO.  
Z8B00003324

SCALE

7.5mm

EUROPEAN PROJECTION

ISSUE DATE  
30-08-2007

REVISION  
01

Testing Conditions



Figure A. Definition of switching times

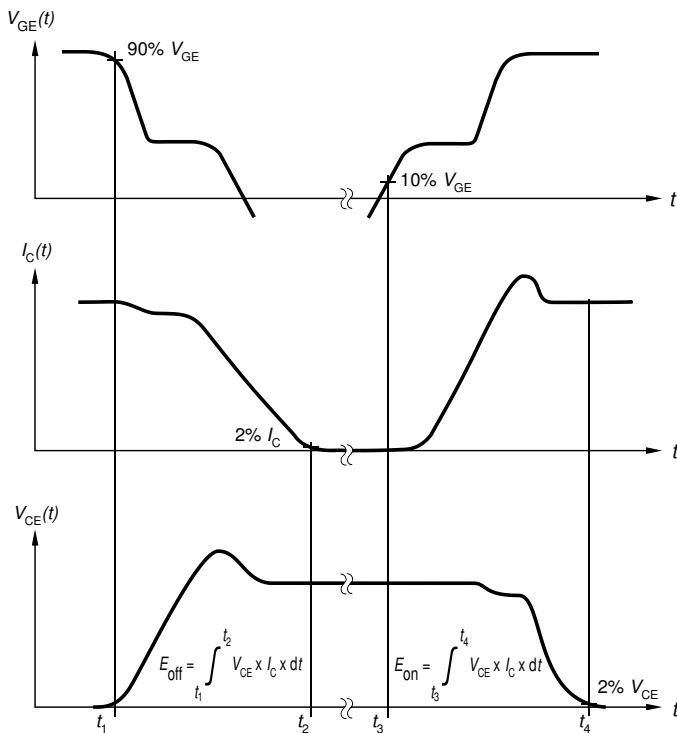


Figure B. Definition of switching losses



Figure C. Definition of diode switching characteristics



Figure D. Thermal equivalent circuit



Figure E. Dynamic test circuit  
Parasitic inductance  $L_{\sigma}$ ,  
parasitic capacitor  $C_{\sigma}$ ,  
relief capacitor  $C_r$ ,  
(only for ZVT switching)

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High speed switching series fifth generation

## Revision History

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AIGB50N65F5

**Revision: 2019-10-19, Rev. 2.1**

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Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2019-10-19	Final Datasheet